

Migration from SkyHigh S34ML-2 to S34ML-3 4K Page SLC NAND

Author: Mohammad Nada

Associated Part Families: S34ML-2, S34ML-3

AN222048 details how to migrate existing designs from SkyHigh S34ML-2 NAND flash memory (S34ML04G2) to SkyHigh S34ML-3 NAND flash memory (S34ML04G3-4K page).

1 Introduction

This application note summarizes the differences between the SkyHigh S34ML04G2 and S34ML04G3 NAND flash memory families and details how to migrate designs from S34ML04G2 to S34ML04G3. S34ML04G2 devices are 3.3 V NAND flash memory parts manufactured with 32-nm technology. S34ML04G3 devices are 3.3 V NAND flash memory parts manufactured with 16-nm technology.

Note: The information provided in this application note focuses on the differences between the two device families. See the respective datasheets for more information and full specifications.

2 Feature Overview

Many features of the two device families are identical. For example, SkyHigh S34ML04G2 NAND flash devices are compatible with the S34ML04G3 NAND flash; both have the following similar characteristics:

- Unique ID (serial number)
- One-Time-Programmable (OTP) area
- 10 years data retention
- ONFI 1.0 compliance
- JEDEC standard-compliant software command set

Table 1 lists the important differences.

Table 1. Feature Differences

Features	S34ML04G2	S34ML04G3
Page size	2KB	4KB
Spare area per page	128 bytes	256 bytes
Number of planes	2	1
Good blocks at shipment time	2	8
Page read (t_R)	30 μ s max	55 μ s typ
Block erase time (t_{BERS} typ)	3.5 ms	4.0 ms
Get features/Set features	-	✓
User level ECC correction	4-bit	0-bit
Volatile/Permanent block protection	-	✓
Volatile block protection	-	✓
Permanent block protection	-	✓
Cache read/write	✓	-

Features	S34ML04G2	S34ML04G3
Read cycle time (t_{RC} min)	25 ns (ONFI mode 4)	20 ns (ONFI mode 5)
Program time (t_{PROG} typ)	200 μ s	400 μ s
Reliability	100,000 P/E cycles	80,000 P/E cycles (-40°C to 85°C)
OTP Block	0	3
Packages	TSOP-48, BGA-63	TSOP-48, BGA-63, BGA-67

3 Device Identification and Configuration

Table 2 lists the differences in ONFI Parameter Page between S34ML04G2 and S34ML04G3. Software that uses dynamic adaptive ONFI probing should work without changes.

Table 2. ONFI Parameter Page Differences

Byte	Description	S34ML04G2	S34ML04G3
6-7	Features supported [4] odd to even page copyback [3] interleaved operations [2] non-sequential page program [1] multiple LUN operations [0] 16-bit data bus width	1Ch, 00h	10h, 00h
8-9	Optional commands supported [5] Read Unique ID [4] Copyback [3] Read Status Enhanced [2] Get/Set Features [1] Read Cache [0] Page Cache Program	3Bh, 00h	3Ch, 00h
44-63	Device model	S34ML04G2: 53h, 33h, 34h, 4Dh, 4Ch, 30h, 34h, 47h, 32h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h	S34ML04G3: 53h, 33h, 34h, 4Dh, 4Ch, 30h, 34h, 47h, 33h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h, 20h
80-83	Number of data bytes per page	00h, 08h, 00h, 00h	00h, 10h, 00h, 00h
84-85	Number of spare bytes / page	80h, 00h	00h, 01h
86-89	Number of data bytes per partial page	00h, 00h, 00h, 00h	00h, 04h, 00h, 00h
90-91	Number of spare bytes / partial page	00h, 00h	40h, 00h
96-99	Number of blocks per logical unit (LUN)	00h, 10h, 00h, 00h	00h, 08h, 00h, 00h
103-104	Number of blocks per logical unit (LUN)	50h, 00h	28h, 00h
105-106	Block endurance	01h, 05h	08h, 04h (-40°C to 85°C) 06h, 04h (-40°C to 105°C)
107	Guaranteed valid blocks at beginning	01h	08h
108-109	Endurance for guaranteed valid blocks	01h, 03h	00h, 00h
112	Number of bits ECC correctability	04h	00h
113	Number of interleaved address bits	01h	01h
114	Interleaved operation attributes [3] Address restrictions for program cache [2] program cache supported [1] no block address restrictions [0] interleaving support	04h	00h

Byte	Description	S34ML04G2	S34ML04G3
129-130	Timing mode support [5] timing mode 5 [4] timing mode 4 [3] timing mode 3 [2] timing mode 2 [1] timing mode 1 [0] timing mode 0	1Fh, 00h	3Fh, 00h
131-132	Program Cache timing mode support [5] timing mode 5 [4] timing mode 4 [3] timing mode 3 [2] timing mode 2 [1] timing mode 1 [0] timing mode 0	1Fh, 00h	00h, 00h
133-134	Maximum page program time (μ s)	BCh, 02h	58h, 02h
137-138	Maximum page read time (μ s)	1Eh, 00h	5E, 01h
254-255	Integrity CRC	28h, A1h	ABh, C0h (–40°C to 85°C) 21h, E8h (–40°C to 105°C)

Table 3 shows the device IDs for the S34ML04G2 and S34ML04G3 devices. If software uses a hardcoded device ID parameter table, new entries for S34ML04G3 must be added.

Table 3. Device IDs

Command	S34ML04G2	S34ML04G3
Read ID	01h, DCh, 90h, 95h, 56h (4 Gb)	01h, DCh, 00h, 1Ah, 00h (4 Gb)

4 AC Characteristics

The S34ML04G2 and S34ML04G3 devices have mainly AC-compatible specifications. Table 4 lists the differences in AC characteristics between the devices. Apart from the page read time (data transfer time from cell to register), the S34ML-3 family is faster in every aspect when compared to the S34ML-2 family. This means that existing S34ML04G2 timings should work fine for S34ML04G3 parts.

Table 4. AC Characteristics Differences

Parameter	S34ML04G2	S34ML04G3
CE# setup time (t_{CS} min)	20 ns	15 ns
Data setup time (t_{DS} min)	10 ns	7 ns
Page read (t_R)	25 μ s max (1 Gb), 30 μ s max (2, 4 Gb)	55 μ s typ
Read cycle time (t_{RC} min)	25 ns	20 ns
RE# access time (t_{REA} max)	20 ns	16 ns
RE# high hold time (t_{REH} min)	10 ns	7 ns
RE# pulse width (t_{RP} min)	12 ns	10 ns
Write cycle time (t_{WC} min)	25 ns	20 ns
WE# high hold time (t_{WH} min)	10 ns	7 ns
WE# pulse width (t_{WP} min)	12 ns	10 ns

This also applies to power-on timing requirements. S34ML04G2 devices initialize within 5 ms, whereas S34ML-3 parts require just 3 ms to initialize (after the reset command). For S34ML04G3 parts, it is required to send a reset command (FFh) after power-on and it is recommended to keep WP# LOW during power up and down.

5 DC Characteristics

The S34ML04G2 and S34ML04G3 devices have mainly DC-compatible specifications. [Table 5](#) lists the differences in DC characteristics between the devices. In standby mode, the S34ML04G3 family requires slightly more current than the S34ML04G2 family. The potential impact of these differences should be evaluated and validated.

Table 5. DC Characteristics Differences

Parameter	S34ML04G2	S34ML04G3
Sequential read current ($I_{CC1 \text{ max}}$)	30 mA	35 mA
Program current ($I_{CC2 \text{ max}}$)	30 mA	35 mA
Standby current, CMOS ($I_{CC5 \text{ max}}$)	50 μ A	100 μ A

6 Packages

S34ML04G3 parts are available in TSOP-48, BGA-63 and BGA-67 packages. However, S34ML04G2 does not support BGA-67 package type.

The S34ML04G3 devices adds a new VPE (Volatile Protection Enable) signal that is connected to TSOP-48 pin #38, BGA-63 ball G5 and BGA-67 ball F4, respectively. These pins/balls are NC for the S34ML-2 family and have a weak internal pull-down in S34ML-3 parts to disable the VPE feature if the input is left floating. This guarantees compatibility with existing board layouts.

7 References

Datasheets:

- 002-00499 - S34ML01G2, S34ML02G2, S34ML04G2 1 GB, 2 GB, 4 GB, 3 V, 4-BIT ECC, SLC NAND FLASH MEMORY FOR EMBEDDED
- 002-19822 - S34ML04G3 4 GB, 3 V, 4K PAGE SIZE, x8 I/O, SLC NAND FLASH MEMORY FOR EMBEDDED (ADVANCE)

Document History

Document Title: AN222048 - Migration from SkyHigh S34ML-2 to S34ML-3 4K Page SLC NAND

Document Number: 002-22048

Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	5969799	MNAD	11/17/2017	New Application Note.
*A		MNAD	05/22/2019	Updated to SkyHigh format. Changed 1 bit ECC to 0 bit ECC for S34ML-3 in the Features and Parameter Page sec.
*B		MNAD	10/18/2019	Updated Endurance to 80K P/E cycles for (-40°C to 85°C)